

ISC Silicon NPN Power Transistors

BU113

DESCRIPTION

- Collector-Emitter Voltage-
:V_{CEX(SUS)} = 700V(Min.)
- Collector Current- I_C= 10A

APPLICATIONS

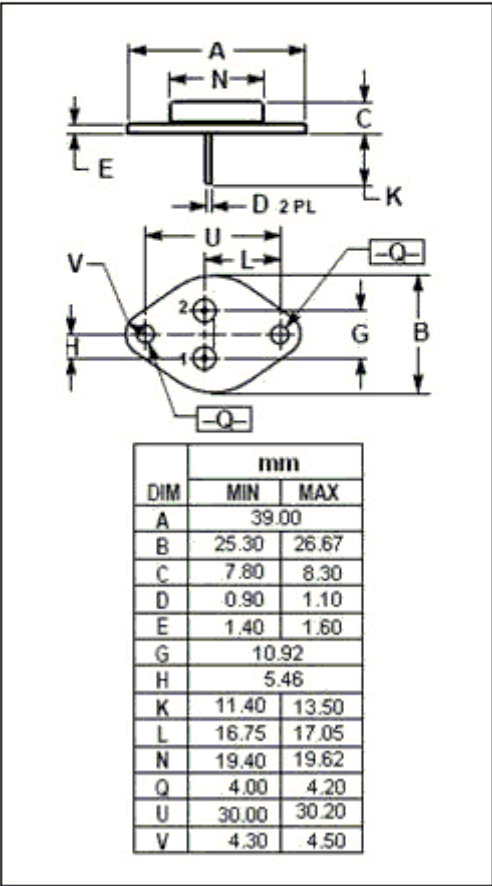
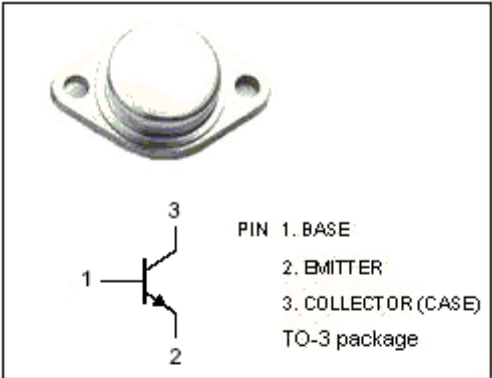
- Designed for use in horizontal deflection output state of color TV receivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Emitter Voltage	700	V
V _{CEX}	Collector-Emitter Voltage V _{BE} = -5V	700	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current-Continuous	10	A
I _B	Base Current-Continuous	4	A
P _C	Collector Power Dissipation @T _C = 90℃	30	W
T _j	Junction Temperature	150	℃
T _{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	2.0	℃/W



ISC Silicon NPN Power Transistors**BU113****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Collector-Base Breakdown Voltage	I _E = 30mA; I _C = 0	10			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 2A			3.0	V
I _{CEX}	Collector Cutoff Current	V _{CE} = 250V; V _{BE} = -5V V _{CE} = 700V; V _{BE} = -5V			2.0 10	mA
h _{FE}	DC Current Gain	I _C = 8A; V _{CE} = 2V	7			
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 4V		6		MHz
C _{OB}	Collector Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		250		pF
t _f	Fall Time	I _C = 8A; I _{B1} = -I _{B2} = 1.6A			1.0	μ s